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To: Commissioner of Patents and Trademarks
Washington, D.C. 20231

Fr: George O. Saile, Reg. No. 19,572
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29-31
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Subject: Serial No. 09/046,007 03/23/98

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A NOVEL SINGLE STRIPE MAGNETORESISTIVE (MR) HEAD

Grp. Art Unit: 2753

INFORMATION DISCLOSURE STATEMENT

Enclosed is Form PTO-1449, Information Disclosure Citation In An Application.

The following Patents and/or Publications are submitted to comply with the duty of disclosure under CFR 1.97-1.99 and 37 CFR 1.56. Copies of each document is included herewith.

Each of these following Patents and/or Publications have been mentioned and described in the Specification of the Subject Patent Application:

U.S. Patent 5,508,866 to Gill et al, "Magnetoresistive Sensor Having Exchange-Coupled Stabilization For Transverse Bias Layer", discloses a soft adjacent layer (SAL) magnetoresistive (MR) sensor element comprising an exchange coupled antiferromagnetic bias layer contacting a SAL within the SAL MR sensor element.

U.S. Patent 5,483,402 to Batra, "Magneto Resistive Head Having Symmetric Off-Track Performance Profile", discloses a soft adjacent layer (SAL) magnetoresistive (MR) sensor element having electrical leads whose planar surfaces are canted with respect to the easy axis of mangetization of the MR layer.

U.S. Patent 5,573,809 to Nix et al, "Process For Forming A Magnetoresistive Device", disclose a soft adjacent layer (SAL) magnetoresistive (MR) sensor element comprising a MR layer having a permanent magnet layer formed at etch of its ends, where the MR layer the permanent magnet layers are separated by a tantalum or titanium spacer layer from a SAL within the SAL magnetoresistive sensor element.

U.S. Patent 5,715,120 to Gill, "Magnetoresistive Sensor With Enhanced Magnetoresistive Effect", discloses a soft adjacent layer (SAL) magnetoresistive (MR) sensor element employing a dielectic spacer layer separating a soft adjacent layer from a magnetoresistive layer within the soft adjacent layer magnetoresistive element, where the SAL is further biased with an antiferromagnetic material layer contacting a surface of the SAL opposite the dielectric layer.

Sincerely,

Stephen B. Ackerman,
Reg. No. 37761